



AMENDMENT TRANSMITTAL LETTER

Docket No.
M4065.0210/P210

Application No.
09/588,008

Filing Date
June 6, 2000

Examiner
Vikki H. Trinh

Art Unit
2814

Applicant(s): Yang, et al.

Invention: IMPROVED MEMORY CELL CAPACITOR STRUCTURE AND METHOD OF FORMATION

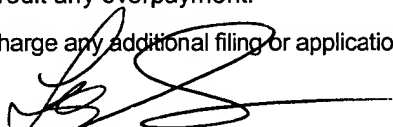
TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	33	- 33 =	0	x	
Independent Claims	3	- 3 =	0	x	
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					

- ☒ Large Entity ☐ Small Entity
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- ☐ Credit any overpayment.
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(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Yang et al.

Application No.: 09/588,008

Group Art Unit: 2814

Filed: June 6, 2000

Examiner: Vikki H. Trinh

For: IMPROVED MEMORY CELL CAPACITOR
STRUCTURE AND METHOD OF
FORMATION

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

This paper is in response to the Office Action dated December 26, 2002. Please amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please rewrite claims 1, 26-28 and 98 as follows:

C1
1. (twice amended) A capacitor for a semiconductor device, said capacitor comprising:

a bottom conducting layer;

a dielectric layer formed over said bottom conducting layer; and

an annealed top conducting layer formed over said dielectric layer, said top conducting layer comprising an oxygen permeable material.